

Appl. No. 10/627,609
Amendment Dated: December 22, 2005
Reply to OA of: September 12, 2005

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-12(canceled).

13(currently amended). A fabrication method of a circuit substrate, comprising:

providing a board;

forming a via in the board;

forming a metal layer on an inner wall of the via;

cutting the via to form a cutting street to separate the metal layer into a plurality of separated metal layers; and

filling an insulator in the via and the cutting street, wherein the material of the insulator is ink.

14(original). The fabrication method of a circuit substrate of claim 13, further comprising:

forming a via land on the board and at the periphery of the via.

15(original). The fabrication method of a circuit substrate of claim 14, wherein cutting the via further separates the via land into a plurality of separated via lands.

16(original). The fabrication method of a circuit substrate of claim 13, wherein the via is a through hole.

17(canceled).

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18(original). The fabrication method of a circuit substrate of claim 13, wherein the via is a blind via.

19(original). The fabrication method of a circuit substrate of claim 13, wherein the material of the metal layer is copper.

20(currently amended). The fabrication method of a circuit substrate of claim 13, wherein the material of the insulator ~~layer~~ is epoxy.

21(canceled).

22(previously presented). The fabrication method of a circuit substrate of claim 13, wherein the board comprises a plurality of insulating layers and conductive trace layers, and the insulating layers are interlaced with the conductive trace layers.

23(original). The fabrication method of a circuit substrate of claim 13, wherein forming the metal layer on the inner wall of the via comprises:

forming an activated film on the inner wall of the via by electro-less plating;
and
forming a metal film on the activated film by plating.

24(original). The fabrication method of a circuit substrate of claim 23, wherein the activated film comprises a conductive polymer film.

25(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises mechanical drilling.

26(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises laser ablation.

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27(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises photochemical reaction.

28(original). The fabrication method of a circuit substrate of claim 13, wherein cutting the via comprises plasma etching.